

**PATENT ASSIGNMENT**

Electronic Version v1.1  
 Stylesheet Version v1.1

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT
<b>CONVEYING PARTY DATA</b>	
<b>Name</b>	<b>Execution Date</b>
David Gao	11/11/2008
Bei Zhu	02/13/2007
Hanming Wu	11/10/2008
John Chen	02/27/2009
Paolo Bonfanti	11/11/2008
<b>RECEIVING PARTY DATA</b>	
<b>Name:</b>	Semiconductor Manufacturing International (Shanghai) Corporation
<b>Street Address:</b>	18 Zhang Jiang Rd., Pudong New Area
<b>City:</b>	Shanghai
<b>State/Country:</b>	CHINA
<b>Postal Code:</b>	201203
<b>PROPERTY NUMBERS Total: 1</b>	
<b>Property Type</b>	<b>Number</b>
Application Number:	12234393
<b>CORRESPONDENCE DATA</b>	
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Correspondent Name:	Townsend and Townsend and Crew LLP
Address Line 1:	Two Embarcadero Center, Eighth Floor
Address Line 4:	San Francisco, CALIFORNIA 94111
ATTORNEY DOCKET NUMBER:	021653-009400US
NAME OF SUBMITTER:	Margaret Stephan

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**Total Attachments: 6**

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Attorney Docket No.: 021653-009400US  
Client Reference No.: I-04-085

ASSIGNMENT OF PATENT APPLICATION

JOINT

WHEREAS, Da Wei Gao of 18 Zhang Jiang Rd., Pudong New Area, Shanghai, 201203 People's Republic of China; Bei Zhu of 18 Zhang Jiang Rd., Pudong New Area, Shanghai, 201203 People's Republic of China; Hanming Wu of 18 Zhang Jiang Rd., Pudong New Area, Shanghai, 201203; John Chen of 18 Zhang Jiang Rd., Pudong New Area, Shanghai, 201203 People's Republic of China; and Paolo Bonfanti of 18 Zhang Jiang Rd., Pudong New Area, Shanghai, 201203 People's Republic of China, hereinafter referred to as "Assignors," are the inventors of the invention described and set forth in the below-identified application for United States Letters Patent:

Title of Invention: A SILICON GERMANIUM AND POLYSILICON GATE STRUCTURE FOR STRAINED SILICON TRANSISTORS

Filing Date: September 19, 2008

Application No.: 12/234,393; and

WHEREAS, Semiconductor Manufacturing International (Shanghai) Corporation, a corporation of People's Republic of China, located at 18 Zhang Jiang Rd, Pudong New Area, Shanghai, 201203, hereinafter referred to as "ASSIGNEE," is desirous of acquiring an interest in the invention and application and in any U.S. Letters Patent and Registrations which may be granted on the same;

For good and valuable consideration, receipt of which is hereby acknowledged by Assignors, Assignors have assigned, and by these presents do assign to Assignee all right, title and interest in and to the invention and application and to all foreign counterparts (including patent, utility model and industrial designs), and in and to any Letters Patent and Registrations which may hereafter be granted on the same in the United States and all countries throughout the world, and to claim the priority from the application as provided by the Paris Convention. The right, title and interest is to be held and enjoyed by Assignee and Assignee's successors and assigns as fully and exclusively as it would have been held and enjoyed by Assignors had this Assignment not been made, for the full term of any Letters Patent and Registrations which may be granted thereon, or of any division, renewal, continuation in whole or in part, substitution, conversion, reissue, prolongation or extension thereof.

Assignors further agree that they will, without charge to Assignee, but at Assignee's expense, (a) cooperate with Assignee in the prosecution of U.S. Patent applications and foreign counterparts on the invention and any improvements, (b) execute, verify, acknowledge and deliver all such further papers, including patent applications and instruments of transfer, and (c) perform such other acts as Assignee lawfully may request to obtain or maintain Letters Patent and Registrations for the invention and improvements in any and all countries, and to vest title thereto in Assignee, or Assignee's successors and assigns.

IN TESTIMONY WHEREOF, Assignors have signed their names on the dates indicated.

Dated: 2008/11/11

David Gao  
Da Wei Gao

Dated: \_\_\_\_\_

Bei Zhu

Dated: 11/10/08

Hanming Wu

Assignment  
Attorney Docket No.: 021653-009400US  
Page 2

Dated: \_\_\_\_\_

\_\_\_\_\_  
John Chen

Dated: 11/11/08

Paolo Bonfanti  
Paolo Bonfanti

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Assignment  
Attorney Docket No.: 021653-009400US  
Page 2

Dated: \_\_\_\_\_

\_\_\_\_\_  
Paolo Bonfanti

Dated: \_\_\_\_\_

\_\_\_\_\_  
Hanming Wu

60578851 v1

ASSIGNMENT OF PATENT APPLICATION

JOINT

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STRUCTURE FOR STRAINED SILICON TRANSISTORS

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IN TESTIMONY WHEREOF, Assignors have signed their names on the dates indicated.

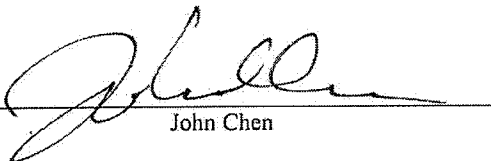
Dated: \_\_\_\_\_  
Da Wei Gao

Dated: \_\_\_\_\_  
Bei Zhu

Dated: \_\_\_\_\_  
Hanming Wu

Assignment  
Attorney Docket No.: 021653-009400US  
Page 2

Dated: 02/27/2009

  
\_\_\_\_\_  
John Chen

Dated: \_\_\_\_\_

\_\_\_\_\_  
Paolo Bonfanti

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